



2SK3351

N-Channel Silicon MOSFET

DC / DC Converter Applications

Features

- Low ON-resistance.
- 4V drive.
- Ultrahigh-speed switching.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		30	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		30	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	60	A
Allowable Power Dissipation	P_D		1	W
		$T_c=25^\circ\text{C}$	30	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}$, $V_{GS}=0$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	1.0		2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=15\text{A}$	14	20		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=15\text{A}$, $V_{GS}=10\text{V}$		11	15	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=4\text{A}$, $V_{GS}=4.5\text{V}$		15	21	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		1450		pF
Output Capacitance	C_{oss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		420		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10\text{V}$, $f=1\text{MHz}$		210		pF

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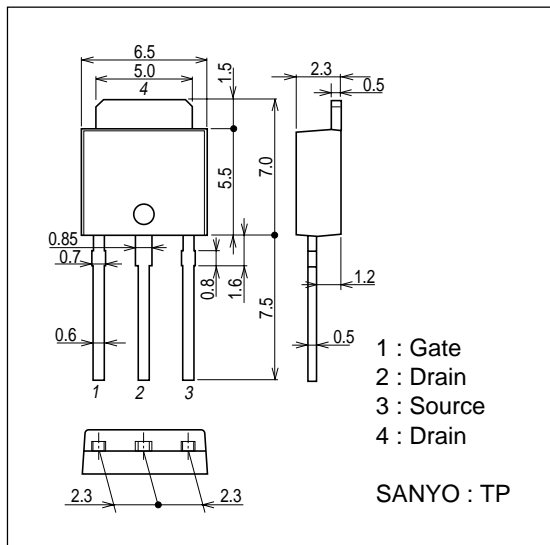
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_d(\text{on})$	See specified Test Circuit.		14		ns
Rise Time	t_r	See specified Test Circuit.		355		ns
Turn-OFF Delay Time	$t_d(\text{off})$	See specified Test Circuit.		110		ns
Fall Time	t_f	See specified Test Circuit.		120		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=30A$		28		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=30A$		4.6		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=30A$		5		nC
Diode Forward Voltage	V_{SD}	$I_S=30A, V_{GS}=0$		0.92	1.2	V

Marking : K3351

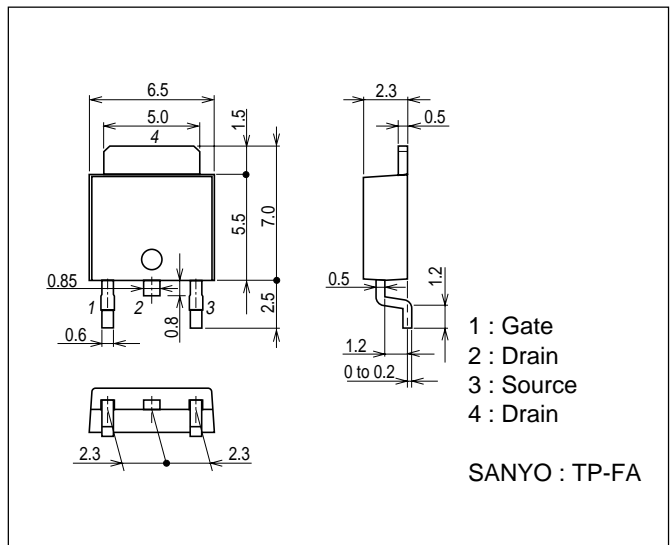
Package Dimensions

unit : mm
2083B

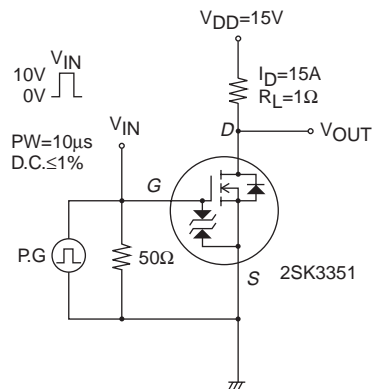


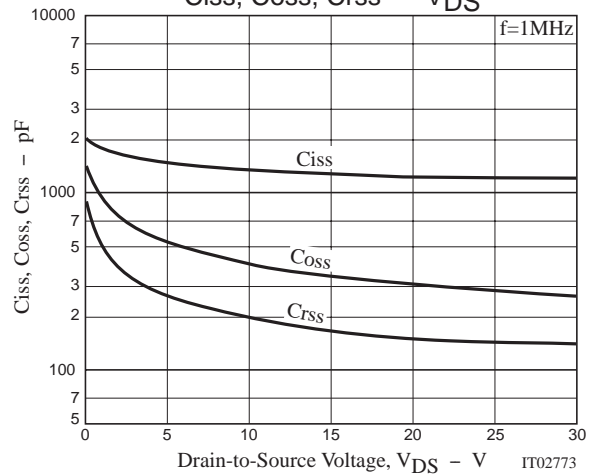
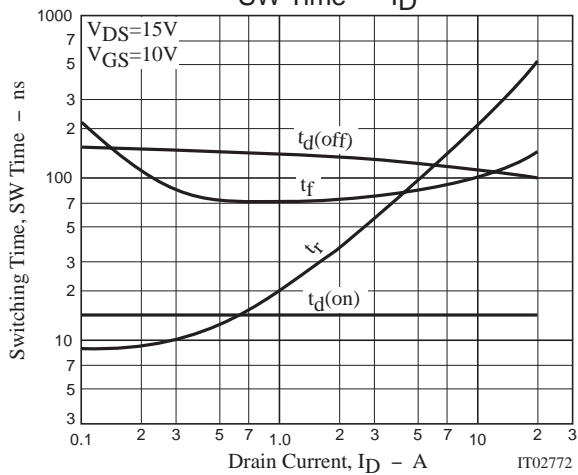
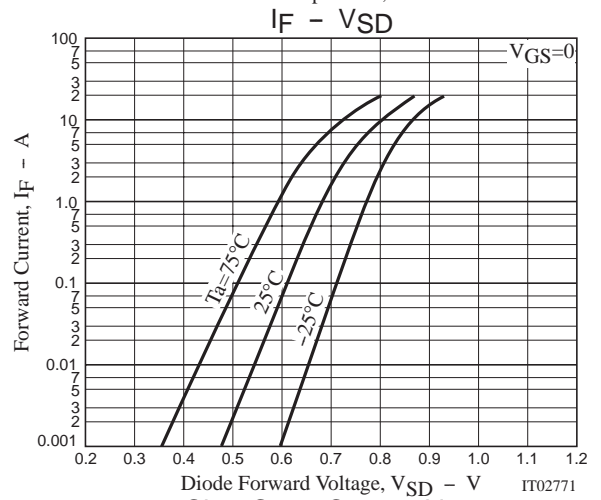
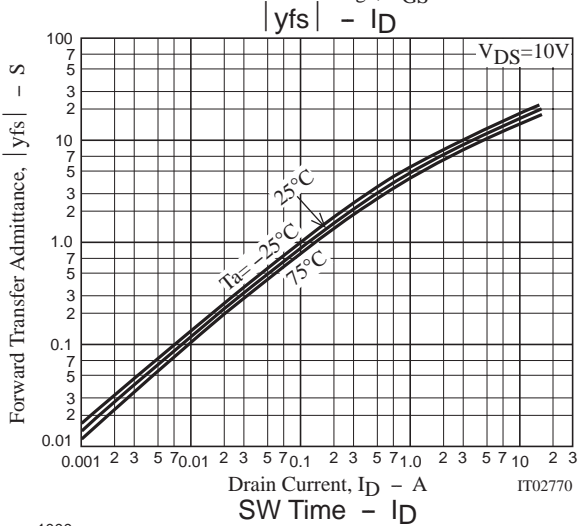
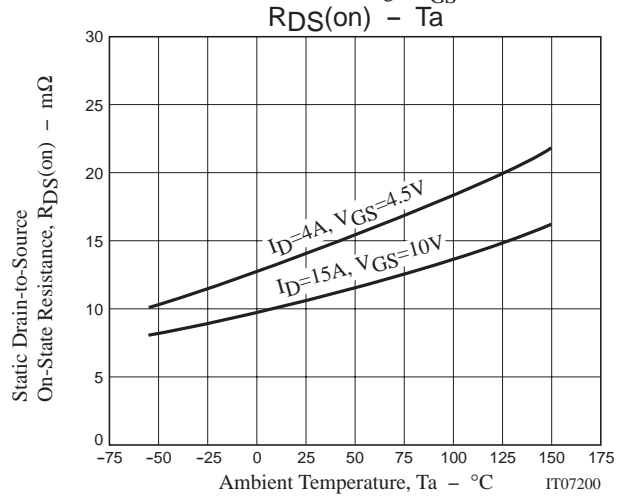
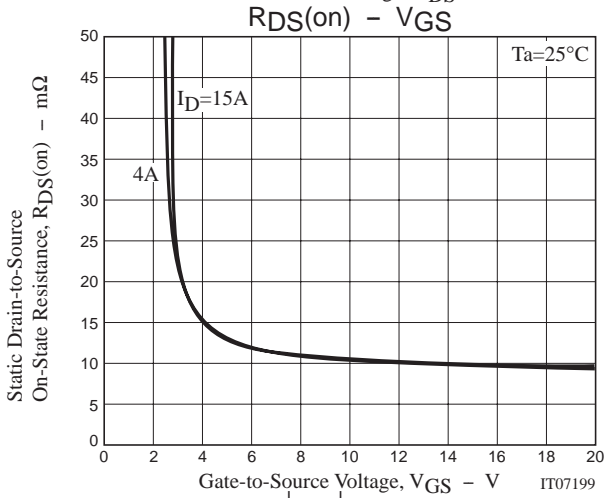
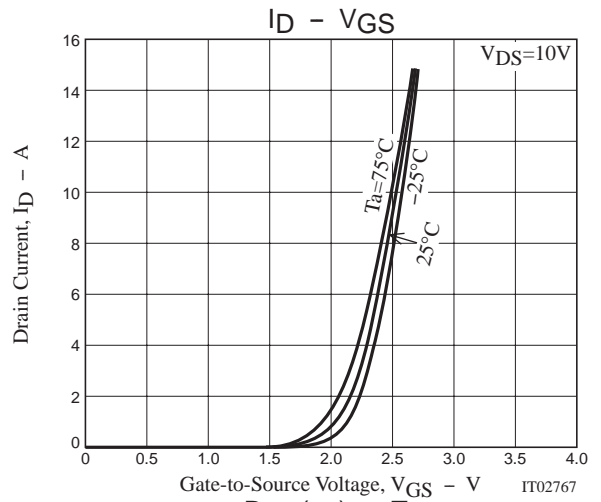
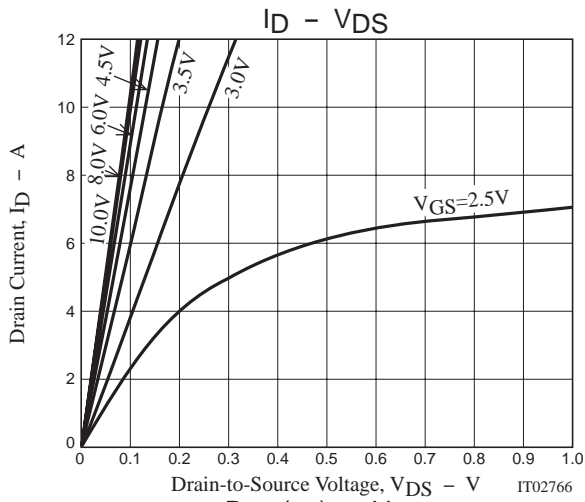
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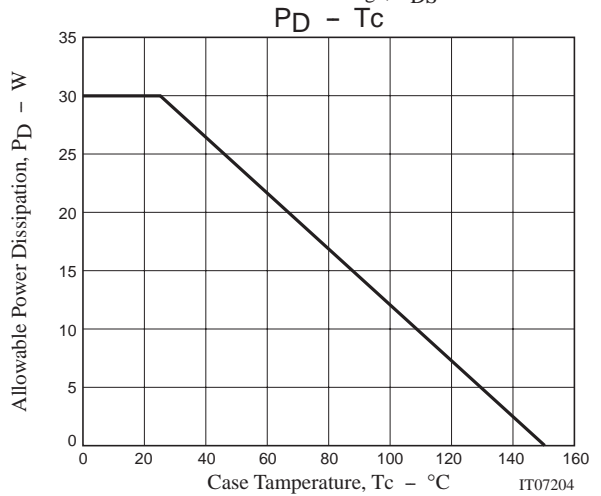
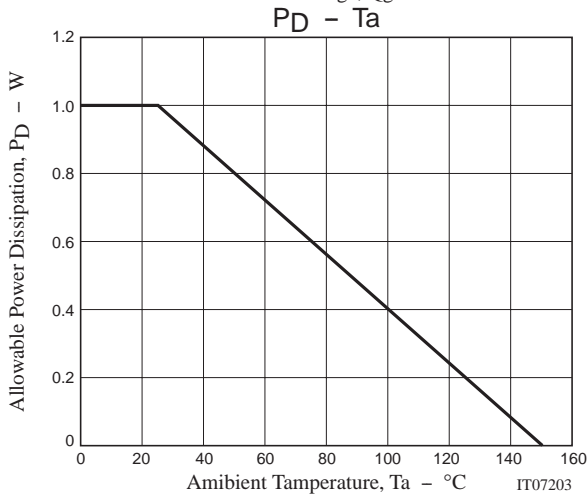
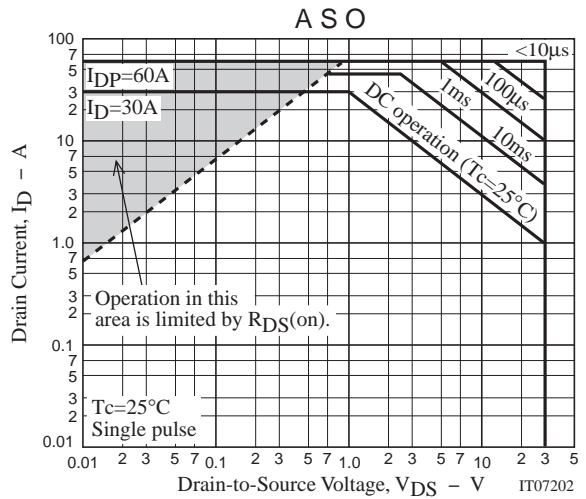
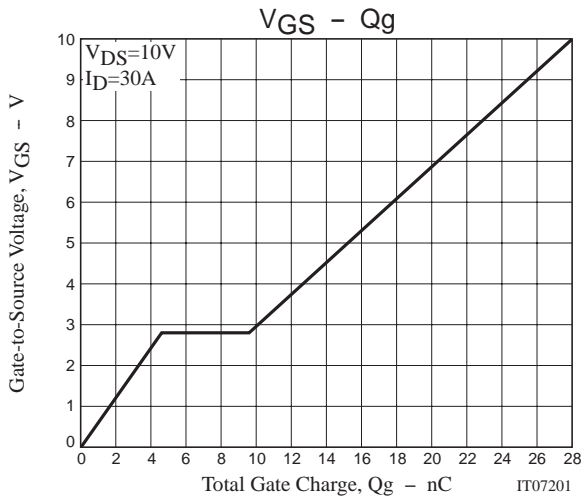
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Switching Time Test Circuit







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